NSN 5962-01-105-1330

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View Online at https://aerobasegroup.com/nsn/5962-01-105-1330 **Body Length:** 0.840 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** Between 0.140 inches and 0.185 inches **Maximum Power Dissipation Rating:** 715.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** Radar set, type an/fps-115 **Features Provided:** Hermetically sealed and monolithic and positive outputs and bipolar and programmable and programmed and 3-state output **Inclosure Material:** Ceramic and glass **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Case Outline Source And Designator:** D-2 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: 5.5 volts power source **Time Rating Per Chacteristic:** 85.00 nanoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Memory Capacity:

Unknown

Test Data Document:

49956-952369 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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